

ABSTRACT

This invention relates to a chemical mechanical polishing slurry comprising polishing grains, ammonium nitrate as an oxidizing agent, 5 1,2,4-triazole as a polishing promoter for a copper metal film and water and having a pH within a range of 3 to 4. The polishing slurry is suitable for forming a damascene copper-based metal interconnection comprising a tantalumr-based metal as a barrier metal film material.